MOSFET – Dual, N-Channel, Small Signal, XLLGA6, 0.65mm x 0.90mm x 0.4mm 20 V, 200 mA

NTND31015NZ

Features

- Dual N-Channel MOSFET
- Offers a Low R_{DS(ON)} Solution in the Ultra Small 0.65 mm x 0.90 mm Package
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Small Signal Load Switch
- Analog Switch
- High Speed Interfacing
- Optimized for Power Management in Ultra Portable Products

MAXIMUM RATINGS ($T_J = 25^{\circ}C$ unless otherwise specified)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage		V_{DSS}	20	V	
Gate-to-Source Voltage			V _{GS}	±8	V
Continuous Drain	Steady	T _A = 25°C	I _D	200	mA
Current (Note 1)	State	T _A = 85°C		140	
	t ≤ 5 s	T _A = 25°C		220	
Power Dissipation (Note 1)	Steady State	T _A = 25°C	P _D	125	mW
	t ≤ 5 s			166	
Pulsed Drain Current $t_p = 10 \mu s$			I _{DM}	800	mA
Operating Junction and Storage Temperature			T _J , T _{STG}	-55 to 150	°C
Source Current (Body Diode) (Note 2)			Is	200	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			TL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

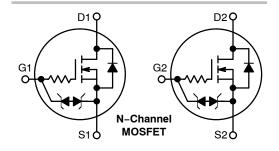
- Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.
- 2. Pulse Test: pulse width $\leq\!300~\mu\text{s},$ duty cycle $\leq\!2\%$



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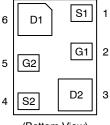
V _{(BR)DSS}	R _{DS(ON)} MAX	I _D Max
20 V	1.5 Ω @ 4.5 V	
	2.0 Ω @ 2.5 V	200 mA
	3.0 Ω @ 1.8 V	200 IIIA
	4.5 Ω @ 1.5 V	





XLLGA6 Case 713AC

PINOUT DIAGRAM



(Bottom View)

MARKING DIAGRAM



D = Specific Device Code

M = Date Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

NTND31015NZ

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit	
Junction-to-Ambient - Steady State (Note 3)	Б	998	0000	
Junction–to–Ambient – t ≤ 5 s (Note 3)	$R_{ hetaJA}$	751	°C/W	

^{3.} Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.

ELECTRICAL CHARACTERISTICS (T₁ = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	on	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•	•					
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 5 V	T _J = 25°C			50	nA
			T _J = 85°C			200	
		V _{GS} = 0 V, V _{DS} = 16 V	T _J = 25°C			100	nA
Gate-to-Source Leakage Current	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 5.0 \text{ V}$				±100	nA
ON CHARACTERISTICS (Note 4)						•	
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_D = 250 \mu A$		0.4		1.0	V
Drain-to-Source On Resistance		V _{GS} = 4.5 V, I _D = 100 mA			0.8	1.5	Ω
		V _{GS} = 2.5 V, I _D = 50 mA			1.1	2.0	
	R _{DS(ON)}	V _{GS} = 1.8 V, I _D = 20 mA			1.4	3.0	
		V _{GS} = 1.5 V, I _D = 10 mA			1.8	4.5	
Forward Transconductance	9FS	V _{DS} = 5.0 V, I _D = 125 mA			0.48		S
Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 10 mA			0.6	1.0	V
CAPACITANCES							
Input Capacitance	C _{ISS}	f = 1 MHz, V _{GS} = 0 V V _{DS} = 15 V			12.3		pF
Output Capacitance	C _{OSS}				3.4		
Reverse Transfer Capacitance	C _{RSS}				2.5		
SWITCHING CHARACTERISTICS, V _{GS} =	4.5 V (Note 4)	•		-	-	<u>'</u>	
Turn-On Delay Time	t _{d(ON)}	V_{GS} = 4.5 V, V_{DD} = 10 V, I_{D} = 200 mA, R_{G} = 3 Ω			16.5		- ns
Rise Time	t _r				25.5		
Turn-Off Delay Time	t _{d(OFF)}				142		
Fall Time	t _f				80		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Package	Shipping [†]
NTND31015NZTAG	XLLGA6 (Pb-Free)	8000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{4.} Switching characteristics are independent of operating junction temperatures.

NTND31015NZ

TYPICAL CHARACTERISTICS

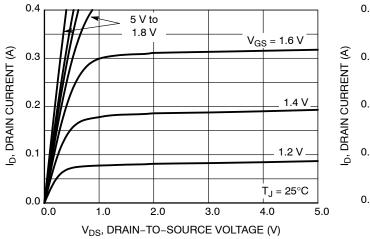


Figure 1. On-Region Characteristics

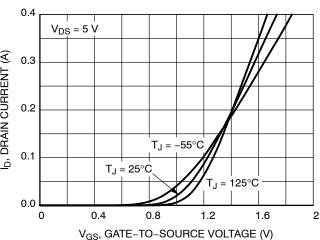


Figure 2. Transfer Characteristics

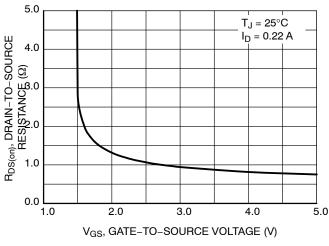


Figure 3. On-Resistance vs. Gate-to-Source Voltage

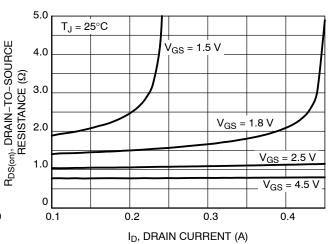


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

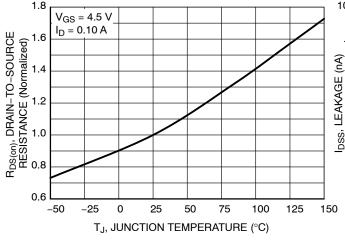


Figure 5. On–Resistance Variation with Temperature

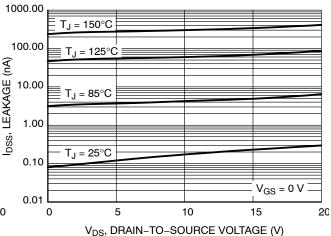
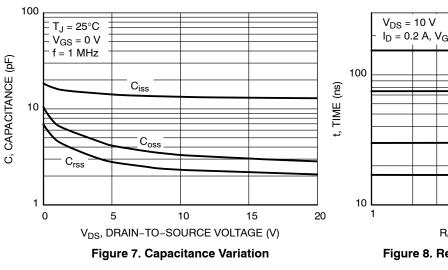


Figure 6. Drain-to-Source Leakage Current vs. Voltage

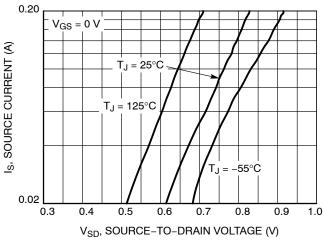
NTND31015NZ

TYPICAL CHARACTERISTICS



 $V_{DS} = 10 \text{ V} \\ -I_D = 0.2 \text{ A, } V_{GS} = 4.5 \text{ V} \\ \hline \\ 100 \\ \hline \\ 10 \\ \hline \\ 10 \\ \hline \\ 10 \\ \hline \\ R_{G}, \text{ GATE RESISTANCE } (\Omega)$

Figure 8. Resistive Switching Time Variation vs. Gate Resistance



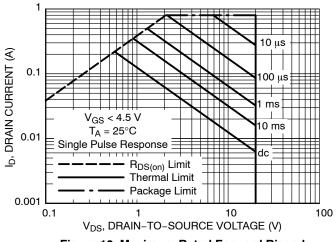


Figure 9. Diode Forward Voltage vs. Current

Figure 10. Maximum Rated Forward Biased Safe Operating Area

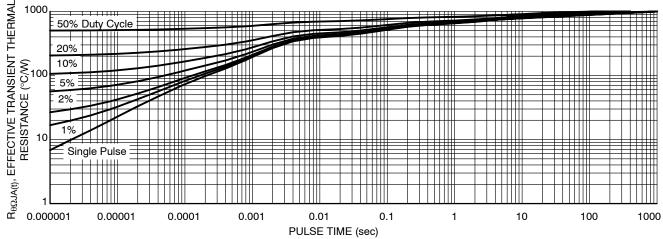
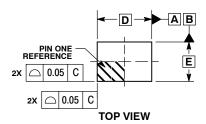


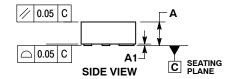
Figure 11. Thermal Response

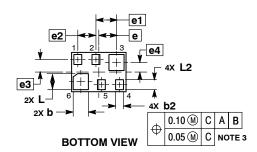


XLLGA6 0.90x0.65 CASE 713AC **ISSUE O**

DATE 19 JUN 2014







- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994 .
 CONTROLLING DIMENSION: MILLIMETERS.
- POSITIONAL TOERANCE APPLIES TO ALL SIX LEADS.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.340	0.440		
A1	0.000	0.050		
b	0.200	0.300		
b2	0.080 0.180			
D	0.900 BSC			
Е	0.650 BSC			
е	0.295 BSC			
e1	0.340 BSC			
e2	0.300 BSC			
е3	0.208 BSC			
e4	0.158 BSC			
L	0.215	0.315		
L2	0.115	0.215		

GENERIC MARKING DIAGRAM*

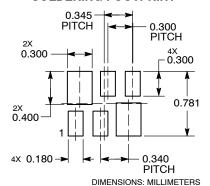


= Specific Device Code Х

= Date Code М

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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